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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)	Art Unit: Unassigned	#440	
Hideomi SUZAWA et al.)	Examiner: Unassigned	M. Bau	nser\
Serial No. 10/086,628)	CERTIFICATE OF MAILING		A log
Filed: March 4, 2002)	I hereby certify that this correspondence is being deposited with		
For: SEMICONDUCTOR DEVICE AND)		The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Gommissioner for Patents,		
MANUFACTURING METHOD)	Washington, D.C. 2023 you 7/5/02		
THEREOF)	SAL		

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

Please preliminarily amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 7 and 11-12 as follows:

- 7. (Amended) A semiconductor device according to claims 1 to 5 wherein a side face of one of the source region and the drain is aligned with one of the source wiring and the electrode.
- 11. (Amended) A method of manufacturing a semiconductor device according to any one of claims 8 or 9 wherein in the eighth step, a part of the first amorphous semiconductor film and the conductive film and the second amorphous semiconductor film are etched with a chlorine type gas.
- 12. (Amended) A method of manufacturing a semiconductor device according to any one of claims 8 or 9 wherein the chlorine type gas is selected from Cl₂ and BCl₃, HCl and SiCl₄ or a gas containing a plurality of gases from these gases.

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